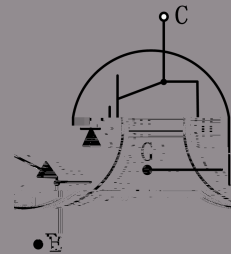
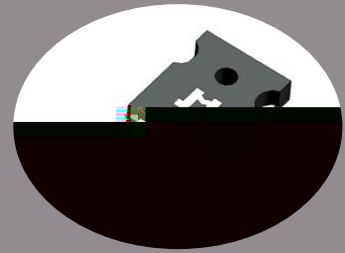


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CES

Collector-emitter voltage

1200

V



E

C<sup>o</sup>

β

S



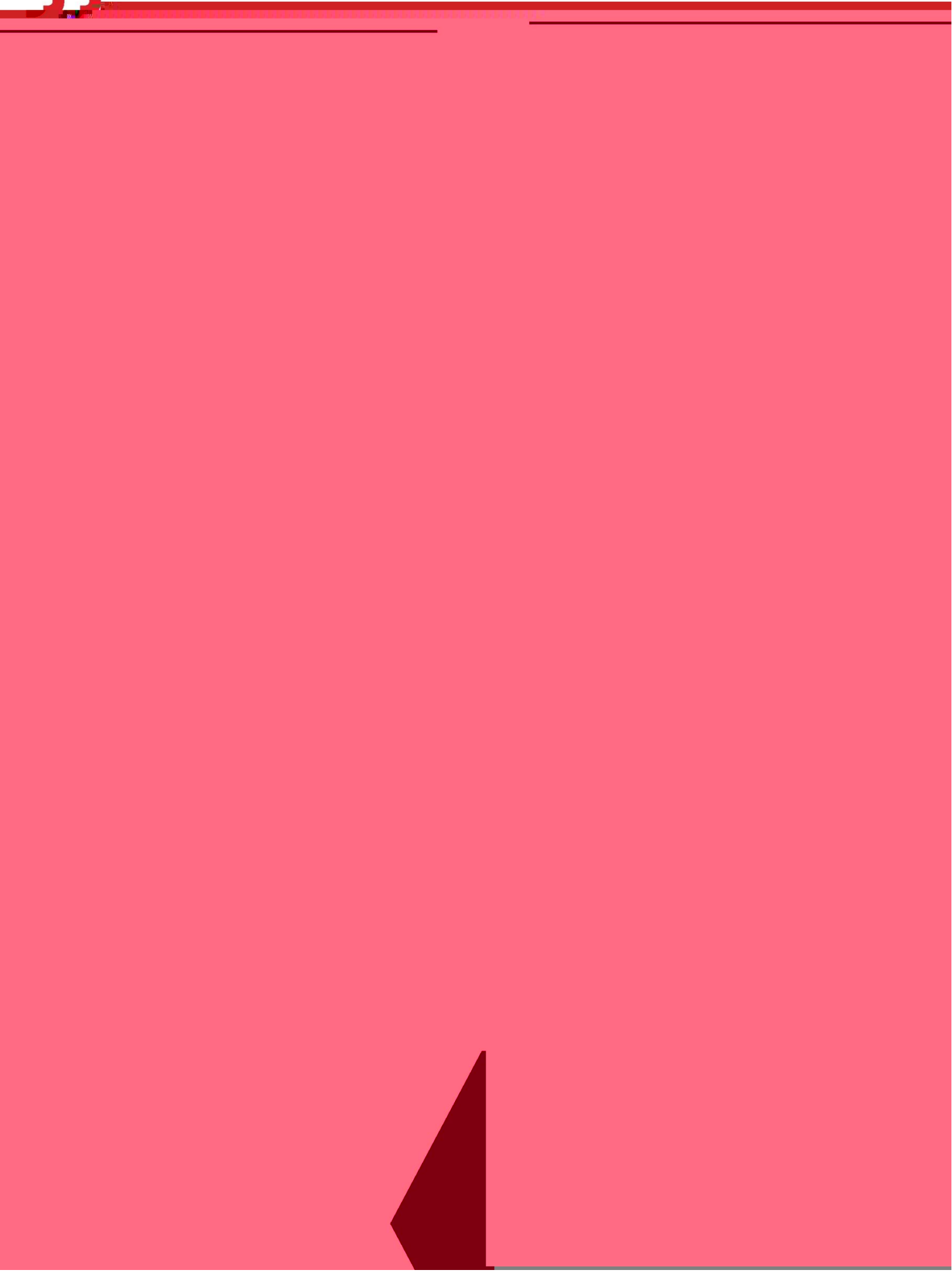
CES	Collector-emitter breakdown voltage	$V_{GE}=0V, I_C=250\mu A$	1200	-	-	V
CES	Collector-emitter leakage current	$V_{CE}=1200V, V_{GE}=0V$	-	-	250	$\mu A$
	Gate leakage current, forward	$V_{GE}=20V, V_{CE}=0V$	-	-	100	nA
GES	Gate leakage current, reverse	$V_{GE}=-20V, I_A$				



d(on)	Turn-on delay time		-	22	-	ns
r	Rise time		-	34	-	ns
d(off)	Turn-off delay time	CC=600V GE=0/15V	-	140	-	ns
f	Fall time	C=15A G=10	-	90	-	ns
on	Turn-on energy	Inductive load	-	0.9	-	mJ
off	Turn-off energy		-	0.7	-	mJ
ts	Total switching energy		-	1.6	-	mJ
d(on)	Turn-on delay time		-	22	-	ns
r	Rise time		-		-	
f	Fall time	CC=600V GE=0/15V C=15A G=10 Inductive load vj =175	-		-	

Impuls





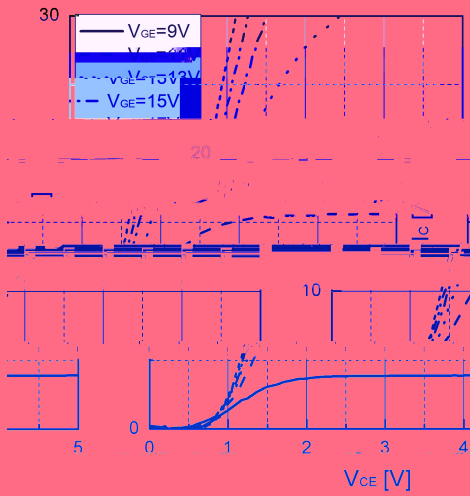


Fig 1. Typical output characteristic (  $v_j=25$  )

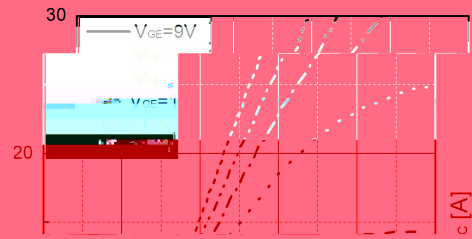


Fig 2. Typical output characteristic(  $v_j=175$  )

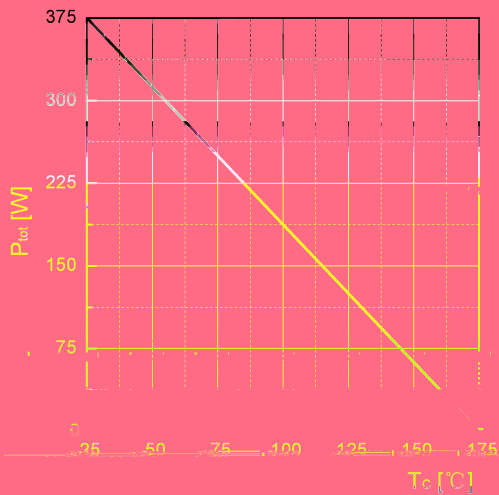


Fig 3. Power dissipation as a function of

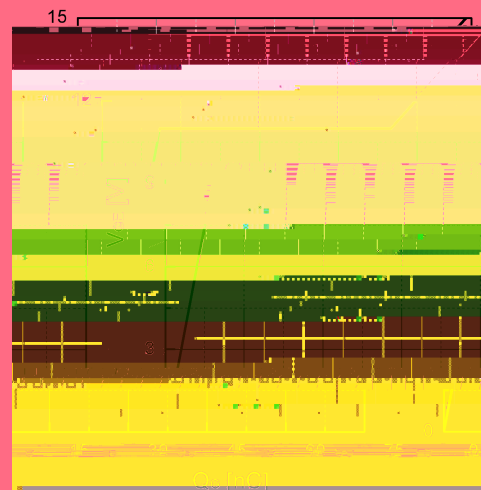


Fig 4. Typical Gate charge

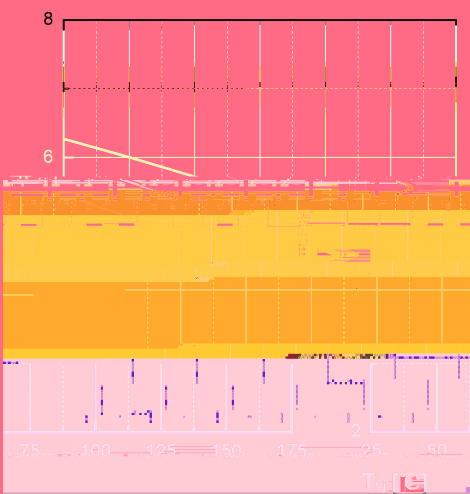


Fig 5. Typical  $V_{GE(th)}$  as a function of  $v_j$  ( $i_c=1mA$ )

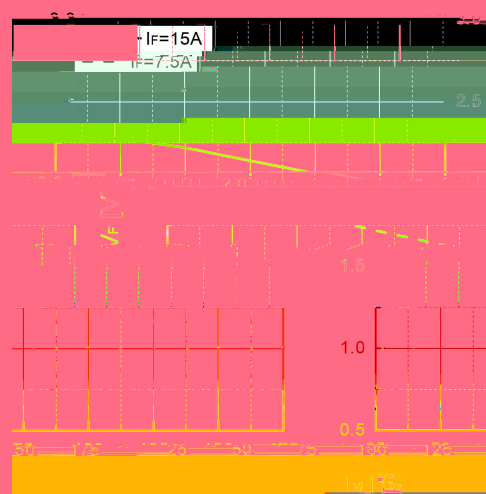
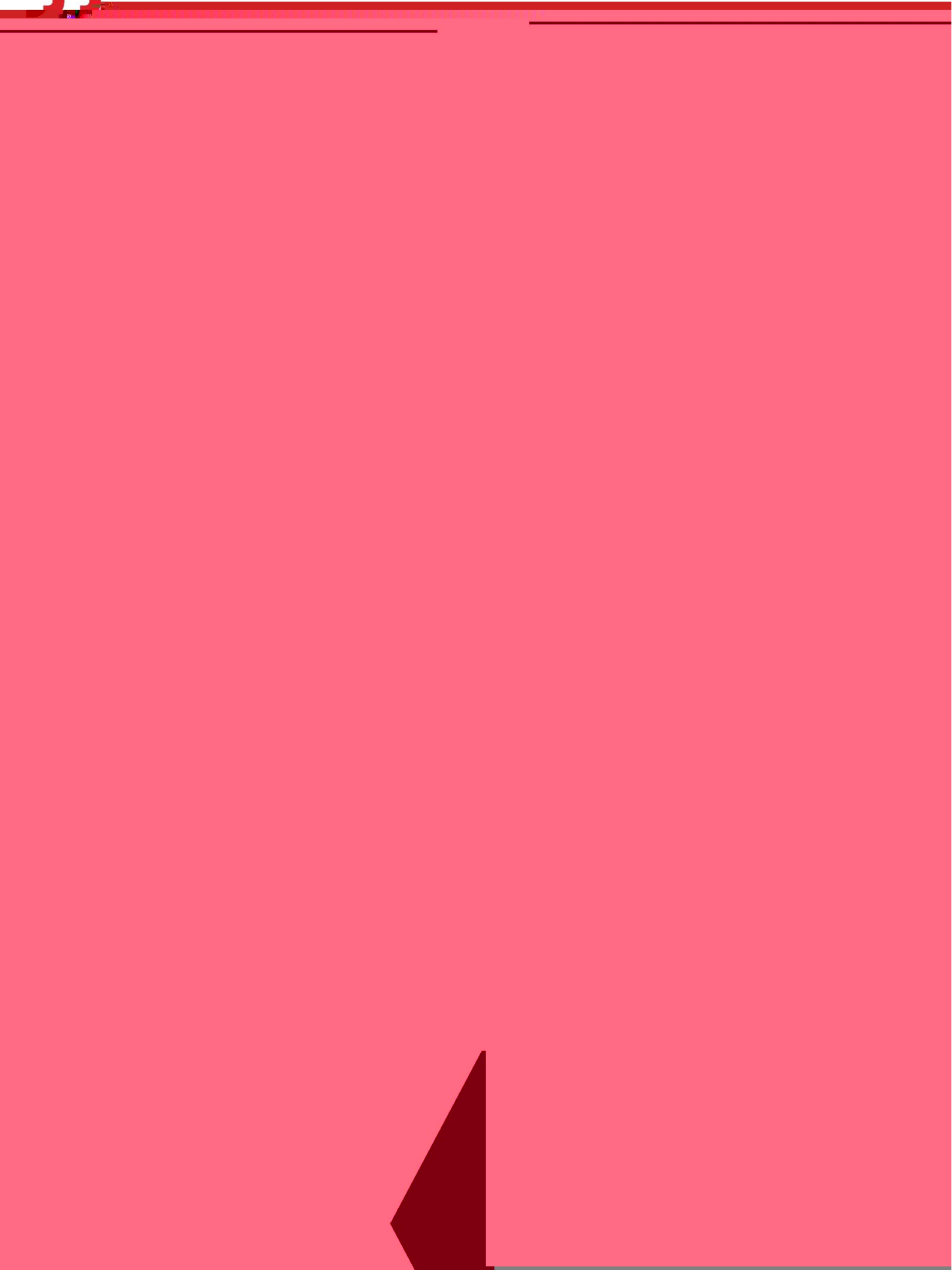


Fig 6. Typical  $V_{CE(F)}$  as a function of  $v_j$



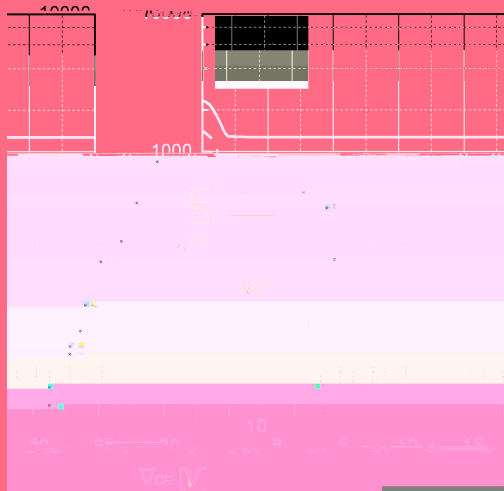


Fig 13. Typical capacitance as a function of  $V_{CE}$   
( $f=1\text{MHz}$ ,  $V_{GE}=0\text{V}$ )

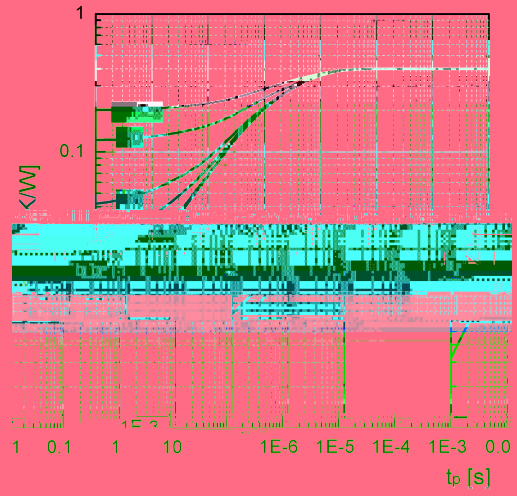
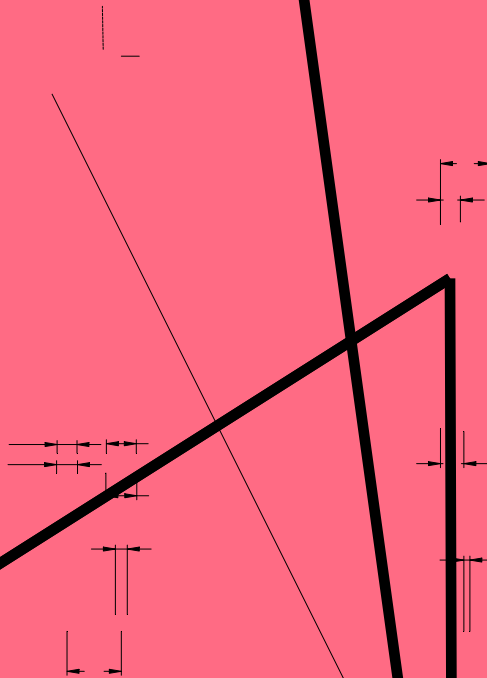


Fig 14. Transient thermal impedance of IGBT



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Dimensions

Dimension	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10	0.622	0.634	
B	20.80	21.00	21.20	0.827	0.835	
C	19.70	20.00	20.30	0.787	0.799	
D	1.80	2.00	2.20	0.079	0.087	
E	1.90	2.10	2.20	0.083	0.091	
F	1.00	1.20	1.40	0.047	0.055	
G	0.25	-	-	0.010	-	0.222
H	4.80	5.00	5.20	0.197	0.205	
J	1.90	2.00	2.10	0.079	0.083	
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.70	0.016	0.024	0.031
M	2.80	3.00	3.20	0.110	0.118	0.126
N	2.90	3.10	3.30	0.114	0.122	0.130



Date	Revision	Changes
2023-12-12	Rev 1.0	Release of the datasheet
2024-03-20	Rev 1.1	Update
2024-05-17	Rev 1.2	Update

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